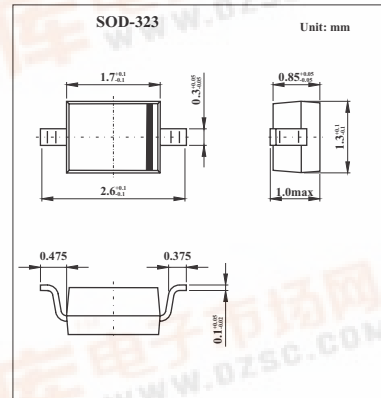


SMD Type Diodes

Silicon Epitaxial Planar Diode
1SV302

Features

- High Capacitance Ratio:C2V/C25V=17.5(Typ.)
- Low Series Resistance:rs=1.05 Ω (Typ.)
- Useful for Small Size Tuner



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	30	V
Peak Reverse Voltage	V _{RM}	35(R _L = 10K Ω)	V
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55 to +125	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V _R	I _R = 1 μ A	30			V
Reverse Current	I _R	V _R = 28 V			10	nA
Capacitance	C _{2V}	f = 1 MHz; V _R = 2 V	42	47	51	pF
	C _{25V}	f = 1 MHz; V _R = 25 V	2.1	2.6	3.1	
Capacitance Ratio	C _{2V} /C _{25V}		17	17.5		
Series Resistance	r _s	V _R = 5V, f = 470 MHz		1.05	1.25	Ω

Note :

Available in matched group for capacitance to 2.5%.

$$\frac{C(\text{Max.})-C(\text{Min.})}{C(\text{Min.})} \leq 0.025$$

(V_R=2~25V)

Marking

Marking	TT
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